

In the Specification**BEST AVAILABLE COPY**

Please amend the title as follows:

~~DEPOSITION APPARATUSES; METHODS FOR ASSESSING ALIGNMENTS OF SUBSTRATES WITHIN DEPOSITION APPARATUSES; AND METHODS FOR ASSESSING THICKNESSES OF DEPOSITED LAYERS WITHIN DEPOSITION APPARATUSES.~~

Please amend paragraph 0049 on page 16 as follows:

[0049] The alignment assessment of Fig. 9 Fig. 10 can be particularly useful for application to epitaxial growth of semiconductor materials, such as, for example, epitaxial growth of silicon, including procedures which selectively epitaxially deposit silicon on particular surfaces relative to others. It is found that misalignment or improper leveling of the substrate by 0.005 inches can result in non-uniform films. Prior art methodologies utilized a level to check alignment of wafers, but such is difficult to accomplish in small chambers, and even when the chambers are large enough, it is difficult to obtain the desired accuracy with a level. Further, it is difficult to employ a level for checking alignment of a spinning substrate. Methodology of the present invention can be utilized to assess alignment of a wafer continuously from an initial period before spinning starts, through the spinning of the wafer, and until a period after the spinning of the substrate has stopped. Alignment in accordance with particular aspects of the present invention can advantageously be conducted with greater precision, better reproducibility/accuracy and better wafer-to-wafer uniformity than prior art methods.